Enhanced stability of defect-based qubits in quantum wells

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Abstract

Optically addressable paramagnetic point defects in semiconductors are among the most promising systems for quantum-information technologies. However, the fidelities of spin initialization and readout rely on optical cycling, and charge-state instabilities during this cycle have proven to be an important unresolved problem. In this work, we demonstrate that the quantum well of an extended defect can stabilize the charge state of a point defect. In particular, we establish that the PL6 center in silicon carbide is a divacancy within a stacking fault, and that the quantum well deriving from this stacking fault stabilizes the defect’s charge state, leading to its extraordinary performance at elevated temperatures and unusual robustness to optical cycling. The generalization of our results provides a material-based solution to the optical instability of color centers in semiconductors that may facilitate the development of a new class of robust single-photon sources and spin qubits.
Introduction
Optically addressable paramagnetic point defects in semiconductors have a strong technological potential in quantum-information processing (1–3) and nanoscale sensing (4–6). Because these technologies rely on optical excitation cycles to initialize and read out the spin of the point defect (7, 8), both long spin coherence times and charge stability during optical excitation are key requirements for the defect. The applied optical illumination, however, often drives undesired ionization processes that degrade the defects desired properties and functionality (9–14) (Fig. 1A-C). This mechanism is an important limitation for all of the most studied point defect qubits, including the nitrogen-vacancy (NV) center in diamond (9, 10, 15, 16), and the divacancy (11–13, 17, 18) and silicon vacancy centers (11, 14, 19, 20) in silicon carbide (SiC).

A promising approach towards solving this problem is to engineer defect ionization energies by locally manipulating the band gap of the host material. In particular, a quantum well can lower the ionization energy of a point defect’s dark state so that the excitation laser will preferentially repopulate the point defect’s bright state. The mechanism is schematically depicted in Fig. 1D.

Here, we demonstrate that the combination of a quantum well and a spin qubit in SiC can stabilize the latter against photoionization. Additionally, we demonstrate that such configurations are readily observable in SiC. The generalization of these exemplified local structures to other semiconductor hosts could provide a material-based solution to the optical instability of color centers and pave the way toward robust point-defect-based single photon emitter and spin qubits.

Results
Stacking faults and polytype inclusions are natural sources of quantum wells in semiconductors (21–23). Such extended defects may additionally incorporate color centers that can exhibit distinct properties compared to their bulk counterparts (24). As both extended defects (25–28) and applicable color centers (17, 20, 29) are commonplace in SiC, we take SiC as an exemplary host material for studying complex
defect structures. In particular, we investigate divacancy qubits in the vicinity of a single
stacking fault in 4H-SiC, in order to understand the consequences of their interaction.

4H-SiC is the most commonly used polytype of SiC. The primitive cells of 4H-SiC and other
relevant polytypes are depicted in Fig. 2A-C. We consider a Frank-type stacking fault
defect (30), a 1FSF(3,2) stacking fault in the Zhdanov notation, whose structure can be
obtained by inserting a single Si-C double layer in cubic stacking order into a perfect 4H-
SiC primitive cell (see in Fig. 2D). This configuration was assigned to the so-called “carrot”
defect in 4H-SiC (23, 31). Stacking faults in 4H-SiC often form quantum-well-like states
that can be observed by photoluminescence (21–23). The considered stacking fault
configuration was assigned to the 482 nm PL-emission line (23).

First, we theoretically confirm that the considered stacking fault forms a quantum well.
The band structure of perfect 4H-and 6H-SiC as well as the defective 4H-SiC structure
including a 1FSF(3,2) stacking fault are depicted in Fig. 3. As can be seen, the stacking
fault gives rise to states below the 4H-SiC conduction band edge that effectively lower
the band gap by 0.24 eV in the vicinity of the stacking fault. The band gap in the defective
4H-SiC resembles the band gap of 6H-SiC. Note, however, that the electron-hole
interaction may further reduce the optical band gap of defective 4H-SiC host. These
results confirm that even a single stacking fault can considerably change the optical
properties of the host material that may influence the stability of qubits.

There are two nonequivalent Si and C sites in the primitive cell of 4H-SiC, see Fig. 2A.
Consequently, point defects usually have more than one nonequivalent configuration
that differ in their second and farther neighbor shells. The configurations of a single site
defect in 4H polytype are marked by h and k referring to a more hexagonal and a more
cubic-like environment, respectively, see Fig. 2A. Divacancy defects, as a clusters of two
adjacent point defects, can have altogether four possible configurations in 4H-SiC, hh, kk,
hk, and kh. Divacancy defects can exhibit either C\textsubscript{3v} or C\textsubscript{1h} symmetry depending on
whether the V\textsubscript{Si}-V\textsubscript{C} axis is parallel or inclined at an angle of ≈109.5° to the c-axis.
Hereinafter, we refer to the high and low symmetry configurations as axial and basal
plane divacancies, respectively. Recently, each of the divacancy configurations were
assigned (32) to the PL1-PL4 divacancy related qubits (17) in 4H-SiC.
In our study, we consider two sets of divacancy configurations within a single model: 1) divacancies in the near-stacking-fault region, i.e. maximally 5 Å away from the stacking fault, and 2) bulk-like divacancy configurations, i.e. at least 14 Å away from the stacking fault. The near-stacking-fault and the bulk-like configurations are marked as \(ab\)-ssf and \(ab\)-4H in see Fig. 2D, respectively. In this notation, \(a\) and \(b\) can respectively represent silicon and carbon vacancies in both hexagonal-like and cubic-like environment. Note that due to the presence of the stacking fault, we distinguish three cubic-like lattice sites in the near stacking fault region, named as \(k_1\), \(k_2\) and \(k_3\), and two hexagonal-like lattice sites in the near-stacking-fault region, named as \(h_1\) and \(h_2\).

In Fig. 4, one can see the calculated hyperfine splitting, \(A_z = (A_{yz}^2 + A_{xz}^2 + A_{zz}^2)^{1/2}\) for all the considered axial configurations depicted in Fig. 2D. These configurations form three clearly distinguishable groups, as shown in Fig. 4(A and B) for the \(Si_{IIa}\) and \(Si_{IIb}\) nuclei sites, respectively. All of the quasi hexagonal configurations, including both bulk-like and near-stacking-fault ones, possess nearly identical \(A_z\) parameters. On the other hand, the quasi-cubic configurations form two subgroups. The bulk-like \(kk\)-4H and the near-stacking-fault \(k_1k_2\)-ssf and \(k_3k_3\)-ssf configurations have similar hyperfine splitting values, while the \(k_2k_3\)-ssf configuration, due to the stacking fault itself, is distinguishable from all of the bulk like divacancies. Considering the basal plane configurations (Fig. 5) for the \(Si_{IIa}\) and \(Si_{IIb}\) nuclei sites, the \(k_3h_2\)-ssf and \(h_2k_2\)-ssf divacancies can be paired with the bulk-like \(kh\)-4H and \(hk\)-4H configurations, while the \(k_1h_1\)-ssf and \(k_3k_1\)-ssf configurations are distinguishable from the rest of the basal-plane configurations.

In Fig. 6 and Table S1 in Supplementary Materials, we provide the calculated zero-field-splitting parameters for all the considered axial and basal plane configurations, respectively. In agreement with the hyperfine splitting results, ZFSs of the axial configurations form three well-distinguishable groups, see Fig. 6. Note that \(k_2k_3\)-ssf configuration exhibits the largest zero-field-splitting that differs from all the bulk-like axial configurations. Considering the basal plane configurations in Table S1 in Supplementary Materials, a similar trend can be observed as for the hyperfine splitting parameters, i.e. \(kh\)-4H and \(k_3h_2\)-ssf as well as \(hk\)-4H and \(h_2k_2\)-ssf pairs exhibit comparable zero-field-splitting parameters.
These results demonstrate that a single 1FSF(3,2) Frank type stacking fault in 4H-SiC has only a perturbative effect on the spin density and derive properties of most of the divacancy configurations in the near-stacking-fault region. Indeed, from the nine considered near stacking fault configurations only three, one axial and two basal plane configurations can be distinguished from the bulk configurations. On the other hand, the distinguishable configurations still exhibit divacancy-like properties. Having either nearly identical or similar properties to bulk divacancies, stacking fault-divacancy complex configurations may give rise to additional divacancy-like qubits in SiC. We further support this statement by calculating the zero-phonon photo luminescence energies in the Supplementary Materials. We find that the divacancy-stacking fault configurations have ZPL energy comparable with those of bulk like divacancy configurations.

While the stacking fault does not significantly alter the considered intrinsic magneto-optical properties of divacancy qubits, the 0.24 eV lowering of the conduction band edge can change the threshold energies of the photo-ionization processes that involve transitions from defect states to the conduction band. Since the negative charge state is the dark state of divacancy qubit (see Ref. (11) and Supplementary Materials), the quantum well of a stacking fault can give rise to a repopulation mechanism that can stabilize the bright state of divacancy qubits, as schematically shown in Fig. 1.

There are two major requirements for this stabilization mechanism: 1) The defect state should not shift toward the valence band maximum (VBM) in the stacking fault configurations to ensure the reduction of defect-conduction band edge transition energies. 2) Defect-quantum well transitions must have sufficient transition strength to ensure fast repopulation of the bright state. We investigate the fulfillment of these requirements (see Supplementary Materials) and find that the divacancy defect state do not lower due to the stacking fault and the transition to the stacking fault state in the dark negative charge state can be as strong as the transition to the conduction band edge. Therefore, we conclude that quantum well of the considered stacking fault can stabilize divacancy qubits.

The concentration for point defect-stacking fault complexes are expected to be low in high purity, high quality samples. Recent ODMR (33) and PL (13) measurements in 4H-SiC, on the other hand, reported additional divacancy-like color centers, PL5-PL7 (33) and
PL5’-PL6’ (13), that cannot be explained by the possible configurations in perfect bulk 4H-SiC host (PL1-PL4 centers (32)). In many respects, these unexplained, yet generally observable configurations follow the properties of bulk divacancy configurations. On the other hand, they show outstanding stability in room-temperature ODMR measurement (17, 33) and photo ionization studies (11). In the latter case, the luminescence of the additional centers, such as the PL6 axial divacancy related room-temperature qubit, do not change by applying an additional repump laser of varying wavelength (11). This is in contrast to the bulk divacancy configurations that exhibit three orders of magnitude increase in the PL intensity by applying an appropriate repump laser (11). This observation indicates that PL6 qubit remains in its bright state under continuous excitation, while bulk divacancy configurations turn into the dark state with higher probability (11).

We propose that the additional divacancy related qubits are related to divacancy-quantum well structures created by a single stacking fault. Indeed, we found three distinguishable configurations, two basal plane and one axial configuration, that can account for the PL5 and PL7 basal plane and PL6 axial divacancy configurations reported in ODMR measurement in 4H-SiC. Furthermore, the calculated hyperfine, zero-field-splitting, and ZPL magneto-optical parameters obtained for the $k_2k_2$-ssf configuration agree well with the experimental data reported for PL6 divacancy related qubit (see Fig. 4, Fig. 6, and Supplementary Materials). Consequently, we assign the $k_2k_2$-ssf combined stacking fault-divacancy configuration to the PL6. The outstanding stability of PL6 qubit may be attributed to the mechanism discussed above and depicted in Fig. 1D.

The observed two additional basal plane divacancy configurations, $k_1h_1$-ssf and $k_2k_1$-ssf, may be related to the additional two basal plane ODMR centers, PL5 and PL7 (33). Due to the fewer experimental data available for PL5 and PL7 qubits, we cannot conclusively assign them at this point.

Finally, we discuss intentional creation of point defect-stacking fault complexes in SiC. Stacking faults may appear in enhanced concentration close to the surface of as-purchased SiC wafers due to surface polishing (34). Consequently, point defect-stacking fault complexes are expected in higher concentration in the near surface region of a sample. To experimentally observe the spatial distribution of these defects in the sample, we carry out ODMR measurements in an inhomogeneous magnetic field to locate
different axial divacancy related qubits in the sample (see Supplementary Materials for the case PL6 qubit). We find that the spatial distribution of the PL6 qubits is significantly different from that of the PL1-PL4 divacancies. Whereas the PL1-PL4 divacancies are approximately uniformly distributed through the sample, the PL6 qubits are concentrated at the surfaces, where the concentration of stacking faults is expected to be higher.

Furthermore, there are numerous ways to create stacking faults in SiC. For example, stacking faults can appear due to different fabrication treatments, such as doping (26), implantation (35), irradiation (36), annealing (26), plastic deformation (37), surface polishing (34), and even due to optical irradiation (38). The PL signal of the stacking fault can be utilized to locate a single isolated stacking fault in the sample. The implantation of positive ions allows point defects to be engineered at well-defined positions in all three dimensions in order to create the point defects where the targeted stacking fault is located.

**Discussion**

The study of point defects embedded in extended defects (39) has received much less attention than that of pure point defects (24). These structures, however, may broaden the palette of point defect qubits and may provide a new avenue for engineering their properties for superior functionality. Through the example of divacancy qubits in close vicinity of a single stacking fault in 4H-SiC, we draw attention to an alternative way of engineering point defect qubit for robust quantum bits.

In particular, we demonstrated that quantum well of a stacking fault can give rise to a mechanism that can stabilize point defect qubits without the application of an additional re-pumping laser. Furthermore, by identifying PL6 room-temperature qubit as a divacancy-stacking fault structure, we demonstrated that defects in quantum wells are important and readily observable in ODMR and PL measurements in SiC.

The particular stability of PL6 center exemplified the stabilization mechanism of stacking fault quantum wells, but our results can be generalized to a wide variety of point defect qubits and single-photon emitters in semiconductors. Stacking faults can also appear in other semiconductors. For example, diamond, an important material for optically
addressable spin qubits, also contains stacking faults (40). Thus, incorporating point defects into quantum wells could be an important strategy for discovering a large and robust class of new spin qubits.

**Methods**

In our first principles density functional theory (DFT) calculations we use Vienna Ab initio Simulation Package (VASP) (41), plane wave basis set of 420 eV, and projector augmented wave method (PAW) (42) to describe electronic states of different defective 4H-SiC supercells. Perdew-Burke-Ernzerhof (PBE) (43) and Heyd-Scuseria-Ernzerhof (HSE06) (44) exchange correlation functionals are employed to include exchange-correlation effects of the many electron system at different levels of approximation. To preserve periodicity, two single stacking faults are included and place 27.8 Å away from each other in our supercell models of fixed 55.7 Å size in the c direction. Following the guidelines of Ref. (32, 45), the basal planar size as well as the k-point grid density are optimized for all the magneto-optical parameters calculated in this study. The large axial size of the supercell allows us to calculate and compare near-stacking-fault and farther, bulk-like divacancies using the same model. To obtain the most accurate ground state hyperfine tensors of first neighbor $^{13}$C and second neighbor $^{29}$Si nuclei, HSE06 functional is used on a PBE relaxed supercell of 704 atoms with 3×3×1 k-point sampling. To obtain the ground state ZFS, we use a 1584 atom supercell with 2×2×1 k-point set, PBE Kohn-Sham wavefunctions, and our in-house implementation for the ZFS tensor calculation (46). In our computational study we concentrate on the most reliable ground state hyperfine and ZFS data, however, to supplement the discussion and our conclusions, we calculate the ZPL energies as well, see Supplementary Materials.

For the band structure calculations, we used HSE06 (44) hybrid functional, 420 eV plane wave cut-off energy and 12×12×6, 12×12×4, and 12×12×1 k-point set for 4H and 6H-SiC and the stacking fault model, respectively.

**References**


Additional references in Supplementary Materials


Acknowledgments

Funding: VI acknowledges the support from the MTA Premium Postdoctoral Research Program. Support from the Swedish Government Strategic Research Areas in Materials Science on Functional Materials at Linköping University (Faculty Grant SFO-Mat-LiU No. 2009-00971) and the Swedish e-Science Centre (SeRC), the Knut & Alice Wallenberg Foundation project “New States of Matter” 2014-2019 (COTXS), the Swedish Research Council (VR 2016-04068), and the Carl-Trygger Stiftelse för Vetenskaplig Forskning (CTS 15:339) is gratefully acknowledged. Analysis of first-principles calculations of defect properties was supported by the Ministry of Education and Science of the Russian Federation (Grant No. 14.Y26.31.0005). Analysis of the model Hamiltonians parameters was supported by the Ministry of Education and Science of the Russian Federation in the
framework of Increase Competitiveness Program of NUST MISIS (No K2-2017-080) implemented by a governmental decree dated 16 March 2013, No 211. AG acknowledges the support from the National Research Development and Innovation Office of Hungary within the Quantum Technology National Excellence Program (Project No. 2017-1.2.1-NKP-2017-00001). The calculations were performed on resources provided by the Swedish National Infrastructure for Computing (SNIC 2016/1-528 and SNIC 2017/11-8) at the National Supercomputer Centre (NSC) and by Linköping University (LiU-2015-00017-60).

**Author contributions:** V.I. wrote the manuscript with input from all authors. Calculations were performed by V.I. and J.D. with input from N.T.S., I.A.A., and A.G. Experiments were performed by A.L.F., P.V.K., and D.D.A. The computational and experimental results were analyzed with contributions from all authors.

**Competing interests:** The authors declare no competing interests.
Fig. 1. A color center whose bright state is stabilized by a quantum well. (A) A bright state of a color center under optical excitation. (B) These incident photons may ionize the defect and turn it into a dark state while also, (C), not have sufficient energy to repopulate the bright state. (D) In a quantum well, however, the excitation laser can successfully re-pump the bright state.
Fig. 2. Primitive cells of common SiC polytypes and the structure of a single Frank-type stacking fault in 4H-SiC. (A, B, and C) show the primitive cells, the stacking sequences, and the possible divacancy nonequivalent configurations in 4H, 6H, and 3C-SiC, respectively. Here, $h$ and $k$ stand for hexagonal-like and cubic-like environments of Si or C sites and the double letters for the vacancy sites of the $V_{Si} - V_{C}$ divacancy pair defect configurations. (D) A single stacking fault in a cubic-like stacking order in 4H-SiC. The close vicinity of the stacking fault resembles the 6H stacking and thus it gives rise to 6H-like additional divacancy configurations in 4H-SiC. The $k_{2}k_{2}$-ssf configuration is assigned to PL6 room-temperature qubits. (E) and (F) depict the spin density of an axial and a basal plane divacancy, respectively. Blue and green filled circles indicate the second neighbor silicon sites for which the hyperfine tensors were calculated.
Fig. 3. Electronic band structure of perfect and defective SiC structures. (A, B, and C) depict the electronic structure of 4H-SiC, 6H-SiC, and defective 4H-SiC including a stacking fault, respectively.
Fig. 4. Diagram of the hyperfine splitting $A_z$ of the considered axial divacancy configurations in 4H-SiC. (A and B) show the hyperfine parameters of Si_{IIa} and Si_{IIb} nuclei sites, respectively. The theoretical results reproduce the experimental trends (47). (C) Calculated hyperfine splitting $A_z$ for the axial divacancy configurations. The considered first and second neighbor sites are shown in Fig. 2(d). The experimental results were reported in Ref. (47). All values are provided in MHz.
**Fig. 5.** Hyperfine splitting of basal plane divacancy configurations. Calculated hyperfine splitting for \(c || B\) for the considered basal plane divacancy configurations, see Fig. 2F. All values are provided in MHz.

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**Fig. 6.** Zero-field-splitting of axial configurations. Zero-field-splitting \(D\) in the ground state of axial divacancy configurations, including both calculated values and experimentally measured \((47)\) ones.

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